

### **INCHANGE SEMICONDUCTOR**

### **isc** Silicon PNP Power Transistor

## 2SA2031

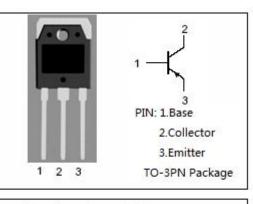
### DESCRIPTION

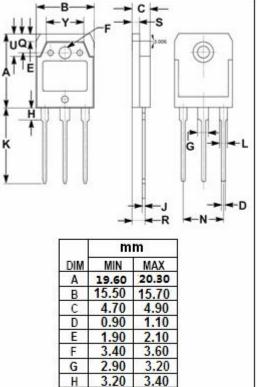
- · Large current capacitance
- · Wide ASO and high durability against breakdown
- Complement to Type 2SC5669
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

• 230V/15A AF100W output application

PARAMETER	VALUE	UNIT
Collector-Base Voltage	-230	v
Collector-Emitter Voltage	-230	V
Emitter-Base Voltage	-6	V
Collector Current-Continuous	-15	A
Collector Current-Pulse	-30	A
Collector Power Dissipation @ $T_c=25^{\circ}C$	140	W
Junction Temperature	150	°C
Storage Temperature Range	-55~150	°C
	Collector-Base Voltage Emitter-Base Voltage Collector Current-Continuous Collector Current-Pulse Collector Power Dissipation @ Tc=25°C Junction Temperature	Collector-Base Voltage-230Collector-Emitter Voltage-230Emitter-Base Voltage-6Collector Current-Continuous-15Collector Current-Pulse-30Collector Power Dissipation @ Tc=25°C140Junction Temperature150





0.605

2.20

10.91

5.10

3.45

J

Κ

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Q

R

s

н Y 0.595 19.80 20.70

1.90

10.89

4.90

3.35

1.995 2.100

5.90 6.20

9.90 | 10.10

1



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### **ELECTRICAL CHARACTERISTICS**

#### Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -50mA ; I <sub>B</sub> = 0	-230			v
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -7.5A; I <sub>B</sub> = -0.75A			-2.0	v
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = -7.5A ; V <sub>CE</sub> = -5V		-1.0	-1.5	v
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -230V ; I <sub>E</sub> =0			-100	μA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> =0			-100	μ Α
hfe-1	DC Current Gain	Ic= -1A ; Vce= -5V	60		160	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -7.5A ; V <sub>CE</sub> = -5V	35			
Сов	Output Capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> = -10V;f <sub>test</sub> = 1.0MHz		200		pF
f⊤	Current-Gain—Bandwidth Product	I <sub>C</sub> =-1A ; V <sub>CE</sub> = -5V		15		MHz

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